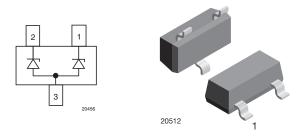
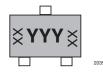
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Two-Line ESD Protection in SOT-23



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MARKING (example only)



YYY = type code (see table below) XX = date code

FEATURES

- Two-line ESD-protection device
- ESD-protection acc. IEC 61000-4-2 ± 30 kV contact discharge ± 30 kV air discharge
- Space saving SOT-23 package
- AEC-Q101 qualified
- e3 Sn
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





COMPLIANT HALOGEN FREE Available



ORDERIN	ORDERING INFORMATION								
	ENVIR	ONMENTAL AN	ID QUALITY CO	DDE	PACKAG	ING CODE			
PART NUMBER (EXAMPLE)	AEC-Q101		RoHS-COMPLIANT + LEAD (Pb)-FREE		3K PER 7" REEL (8 mm TAPE),	10K PER 13" REEL (8 mm TAPE),	ORDERING CODE (EXAMPLE)		
	AMPLE) QUALIFIED STANDARD GREEN PLATED 15K/BOX = MOQ		10K/BOX = MŐQ						
GSOT05C-		E		3	-08		GSOT05C-E3-08		
GSOT05C-			G	3	-08		GSOT05C-G3-08		
GSOT05C-	Н	E		3	-08		GSOT05C-HE3-08		
GSOT05C-	Н		G	3	-08		GSOT05C-HG3-08		
GSOT05C-		E		3		-18	GSOT05C-E3-18		
GSOT05C-			G	3		-18	GSOT05C-G3-18		
GSOT05C-	Н	E		3		-18	GSOT05C-HE3-18		
GSOT05C-	Н		G	3		-18	GSOT05C-HG3-18		

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PACKA	PACKAGE DATA								
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS		
GSOT03C	SOT-23	03C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals		
0501050	001-20	C1G	Green	8.1 mg	01 94 0-0	(according J-STD-020)			
GSOT04C	SOT-23	04C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals		
0501040	001-20	C8G	Green	8.1 mg	01 94 0-0	(according J-STD-020)			
GSOT05C	SOT-23	05C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals		
0501050	001-20	C2G	Green	8.1 mg	02 94 0-0	(according J-STD-020)			
GSOT08C	SOT-23	08C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals		
6301000	301-23	C3G	Green	8.1 mg	0L 94 V-0	(according J-STD-020)			
GSOT12C	SOT-23	12C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals		
0301120	301-23	C4G	Green	8.1 mg	0L 94 V-0	(according J-STD-020)			
GSOT15C	SOT-23	15C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals		
0301130	301-23	C5G	Green	8.1 mg	0L 94 V-0	(according J-STD-020)	200 C/10 S at terminals		
GSOT24C	SOT-23	24C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals		
6301240	301-23	C6G	Green	8.1 mg	01 94 0-0	(according J-STD-020)	200 O/TOSAL LETTIINAIS		
GSOT36C	SOT-23	36C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals		
6301300	301-23	C7G	Green	8.1 mg	02 94 0-0	(according J-STD-020)			

ABSOLUTE MAXIMUM RATINGS GSOT03C					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	I	30	А	
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	IPPM	30	А	
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	P _{PP}	369	W	
Fear puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu$ s; single shot	г рр	504	W	
EQD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	± 30	kV	
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV	
Operating temperature	Junction temperature	Т _Ј	-55 to +150	°C	
Storage temperature		T _{STG}	-55 to +150	°C	

ABSOLUTE MAXIMU	MUM RATINGS GSOT04CTEST CONDITIONSSYMBOLVALUEUNITPin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot 30 APin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot 30 APin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot 429 WPin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot 429 W			
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current			30	А
		IPPM	30	А
		P	429	W
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	564	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV
ESD inimunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV
Operating temperature	Junction temperature	TJ	-55 to +150	°C
Storage temperature		T _{STG}	-55 to +150	°C



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ABSOLUTE MAXIMUM	RATINGS GSOT05C			
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	I	30	А
reak puise current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	IPPM	30	А
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot		480	W
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu$ s; single shot	P _{PP}	612	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV
Operating temperature	Junction temperature	TJ	-55 to +150	°C
Storage temperature		T _{STG}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS GSOT08C					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot		18	A	
reak puise current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu$ s; single shot	IPPM	18	А	
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot		345	W	
r ear puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu$ s; single shot	P _{PP}	400	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV	
	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV	
Operating temperature	Junction temperature	TJ	-55 to +150	°C	
Storage temperature		T _{STG}	-55 to +150	°C	

ABSOLUTE MAXIMU	M RATINGS GSOT12C			
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
5	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot		12	А
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	IPPM	12	А
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	312	W
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	ГРР	337	W
	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV
Operating temperature	Junction temperature	TJ	-55 to +150	°C
Storage temperature		T _{STG}	-55 to +150	°C

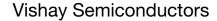


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ABSOLUTE MAXIMUM RATINGS GSOT15C				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot		8	А
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	IPPM	8	А
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	P _{PP}	345	W
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	ГРР	400	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses		± 30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV
Operating temperature	Junction temperature	TJ	-55 to +150	°C
Storage temperature		T _{STG}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS GSOT24C					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t_p = 8/20 µs; single shot	1	5	А	
reak puise current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	IPPM	5	А	
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	P _{PP}	235	W	
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu$ s; single shot	ГРР	240	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV	
ESD infinding	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV	
Operating temperature	Junction temperature	TJ	-55 to +150	°C	
Storage temperature		T _{STG}	-55 to +150	°C	

ABSOLUTE MAXIMUM	RATINGS GSOT36C			
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot		3.5	А
r eak puise current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu$ s; single shot	IPPM	3.5	А
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu$ s; single shot	P _{PP}	248	W
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	ГРР	252	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV
ESD inimunity	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV
Operating temperature	Junction temperature	TJ	-55 to +150	°C
Storage temperature		T _{STG}	-55 to +150	C°



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BIAs-MODE (2-line Bidirectional Asymmetrical protection mode)

With the GSOTxxC two signal- or data-lines (L1, L2) can be protected against voltage transients. With pin 3 connected to ground and pin 1 and pin 2 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified Maximum Reverse Working Voltage (V_{RWM}) the protection diode between pin 2 and pin 3 and between pin 1 and pin 3 offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the breakdown voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The Clamping Voltage (V_C) is defined by the breakdown voltage (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection diode.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction through the protection diode. The low Forward Voltage (V_F) clamps the negative transient close to the ground level.

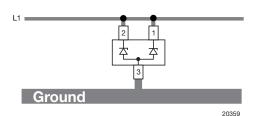
Due to the different clamping levels in forward and reverse direction the GSOTxxC clamping behavior is Bidirectional and Asymmetrical (BiAs).



If a higher surge current or peak pulse current (I_{PP}) is needed, both protection diodes in the GSOTxxC can also be used in parallel in order to "double" the performance.

This offers:

- double surge power = double peak pulse current (2 x I_{PPM})
- half of the line inductance = reduced clamping voltage
- half of the line resistance = reduced clamping voltage
- double line capacitance (2 x C_D)
- double reverse leakage current (2 x I_R)



ELECTRICAL CHARACTERISTICS GSOT03C ($T_{amb} = 25$ °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines
Reverse stand-off voltage	at I _R = 100 μA	V _{RWM}	-	-	3.3	V
Reverse current	at V _R = 3.3 V	I _R	-	-	100	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	4	4.6	-	V
Poverse elemping veltage	at I _{PP} = 1 A	V	-	5.7	7.5	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	10	12.3	V
Forward elemains voltage	at I _{PP} = 1 A	V	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V
Canacitanaa	at $V_R = 0 V$; f = 1 MHz	<u> </u>	-	420	600	pF
Capacitance	at V _R = 1.6 V; f = 1 MHz	C _D	-	260	-	pF

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ELECTRICAL CHARACTERISTICS GSOT04C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	at I _R = 20 μA	V _{RWM}	-	-	4	V		
Reverse current	at V _R = 4 V	I _R	-	-	20	μA		
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	5	6.1	-	V		
Deverse elemning veltage	at I _{PP} = 1 A	N	-	7.5	9	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	11.2	14.3	V		
	at I _{PP} = 1 A	N	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V		
Capacitance	at $V_R = 0 V$; f = 1 MHz	- C _D	-	310	450	pF		
	at V _R = 2 V; f = 1 MHz		-	200	-	pF		

ELECTRICAL CHARACTERISTICS GSOT05C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	at I _R = 10 µA	V _{RWM}	-	-	5	V		
Reverse current	at V _R = 5 V	I _R	-	-	10	μA		
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	6	6.8	-	V		
Deverse elemping veltage	at I _{PP} = 1 A	V	-	7	8.7	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	Vc	-	12	16	V		
Forward elemping valtage	at I _{PP} = 1 A	V	-	1	1.2	V		
Forward clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$	V _F	-	4.5	-	V		
Conceitance	at $V_R = 0$ V; f = 1 MHz		-	260	350	pF		
Capacitance	at V _R = 2.5 V; f = 1 MHz	C _D	-	150	-	pF		

ELECTRICAL CHARACTERISTICS GSOT08C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines			
Reverse stand-off voltage	at I _R = 5 μA	V _{RWM}	-	-	8	V			
Reverse current	at V _R = 8 V	I _R	-	-	5	μA			
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	9	10	-	V			
Poverse elemping veltage	at I _{PP} = 1 A	V	-	10.7	13	V			
Reverse clamping voltage	at I _{PP} = I _{PPM} = 18 A	V _C	-	15.2	19.2	V			
Forward elemping voltage	at I _{PP} = 1 A	V	-	1	1.2	V			
Forward clamping voltage	at Ipp = Ipp _M = 18 A	V _F	-	3	-	V			
Canaaitanaa	at $V_R = 0 V$; f = 1 MHz	_	-	160	250	pF			
Capacitance	at $V_R = 4 V$; f = 1 MHz	C _D	-	80	-	pF			





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ELECTRICAL CHARACTERISTICS GSOT12C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines			
Reverse stand-off voltage	at I _R = 1 μA	V _{RWM}	-	-	12	V			
Reverse current	at V _R = 12 V	I _R	-	-	1	μA			
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	13.5	15	-	V			
Deverse elemning veltage	at I _{PP} = 1 A	N	-	15.4	18.7	V			
Reverse clamping voltage	at I _{PP} = I _{PPM} = 12 A	V _C	-	21.2	26	V			
	at I _{PP} = 1 A	N	-	1	1.2	V			
Forward clamping voltage	at I _{PP} = I _{PPM} = 12 A	V _F	-	2.2	-	V			
Conscitores	at $V_R = 0 V$; f = 1 MHz	- C _D	-	115	150	pF			
Capacitance -	at $V_R = 6 V$; f = 1 MHz		-	50	-	pF			

ELECTRICAL CHARACTERISTICS GSOT15C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines			
Reverse stand-off voltage	at I _R = 1 μA	V _{RWM}	-	-	15	V			
Reverse current	at V _R = 15 V	I _R	-	-	1	μA			
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	16.5	18	-	V			
Deverse elemping veltage	at I _{PP} = 1 A	N	-	19.4	23.5	V			
Reverse clamping voltage	at I _{PP} = I _{PPM} = 8 A	Vc	-	24.8	28.8	V			
Forward elemping valtage	at I _{PP} = 1 A	V	-	1	1.2	V			
Forward clamping voltage	at I _{PP} = I _{PPM} = 8 A	V _F	-	1.8	-	V			
0 II	at $V_R = 0$ V; f = 1 MHz		-	90	120	pF			
Capacitance	at V _R = 7.5 V; f = 1 MHz	C _D	-	35	-	pF			

ELECTRICAL CHARACTERISTICS GSOT24C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines			
Reverse stand-off voltage	at I _R = 1 µA	V _{RWM}	-	-	24	V			
Reverse current	at V _R = 24 V	I _R	-	-	1	μA			
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	27	30	-	V			
Reverse clamping voltage	at I _{PP} = 1 A	V	-	34	41	V			
neverse clamping voltage	at I _{PP} = I _{PPM} = 5 A	V _C	-	41	47	V			
Forward elemping voltage	at I _{PP} = 1 A	V	-	1	1.2	V			
Forward clamping voltage	at I _{PP} = I _{PPM} = 5 A	V _F	-	1.4	-	V			
Capacitanaa	at $V_R = 0 V$; f = 1 MHz	0	-	65	80	pF			
Capacitance	at V _R = 12 V; f = 1 MHz	C _D	-	20	-	pF			

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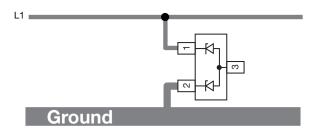
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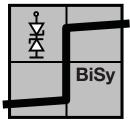
ELECTRICAL CHARACTERISTICS GSOT36C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	at I _R = 1 μA	V _{RWM}	-	-	36	V		
Reverse current	at V _R = 36 V	I _R	-	-	1	μA		
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	39	43	-	V		
Deverse elemping veltage	at I _{PP} = 1 A	V	-	49	60	V		
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 3.5 \text{ A}$	V _C	-	59	71	V		
	at I _{PP} = 1 A	N	-	1	1.2	V		
Forward clamping voltage	at $I_{PP} = I_{PPM} = 3.5 \text{ A}$	V _F	-	1.3	-	V		
Capacitance	at $V_R = 0 V$; f = 1 MHz	- C _D	-	52	65	pF		
	at V _R = 18 V; f = 1 MHz		-	12	-	pF		

BiSy-MODE (1-line bidirectional symmetrical protection mode)

If a bipolar symmetrical protection device is needed the GSOTxxC can also be used as a single line protection device. Therefore pin 1 has to be connected to the signal- or data-line (L1) and pin 2 to ground (or vice versa). Pin 3 must not be connected. Positive and negative voltage transients will be clamped in the same way. The clamping current through the GSOTxxC passes one diode in forward direction and the other one in reverse direction. The clamping voltage (V_c) is defined by the breakthrough voltage (V_{BR}) level of one diode plus the forward voltage of the other diode plus the voltage drop at the series impedances (resistances and inductances) of the protection device.

Due to the same clamping levels in positive and negative direction the GSOTxxC voltage clamping behaviour is bidirectional and symmetrical (BiSy).





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ELECTRICAL CHARACTERISTICS GSOT03C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand-off voltage	at I _R = 100 μA	V _{RWM}	-	-	3.8	V			
Reverse current	at V _R = 3.8 V	I _R	-	-	100	μA			
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	4.5	5.3	-	V			
Reverse clamping voltage	at I _{PP} = 1 A	V	-	7	8.4	V			
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$	V _C	-	14	16.8	V			
Capacitance	at $V_R = 0 V$; f = 1 MHz	- C _D	-	210	300	pF			
	at V _R = 1.6 V; f = 1 MHz		-	190	-	pF			

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	ELECTRICAL CHARACTERISTICS GSOT04C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand-off voltage	at I _R = 20 μA	V _{RWM}	-	-	4.5	V			
Reverse current	at V _R = 4.5 V	I _R	-	-	20	μA			
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	5.5	6.8	-	V			
Poweres elemping veltage	at I _{PP} = 1 A	V	-	7.5	9	V			
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$	V _C	-	15.7	18.8	V			
	at $V_R = 0 V$; f = 1 MHz	<u> </u>	-	155	225	pF			
Capacitance	at V _R = 2 V; f = 1 MHz	C _D	-	135	-	pF			

ELECTRICAL CHARACTERISTICS GSOT05C (T_{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin 1; pin 3 not connected

between pin 1 to pin 2 to pin 2 to pin 1, pin 3 hot connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	at I _R = 10 μA	V _{RWM}	-	-	5.5	V		
Reverse current	at V _R = 5.5 V	I _R	-	-	10	μA		
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	6.5	7.5	-	V		
Reverse clamping voltage	at I _{PP} = 1 A	M.	-	8.1	9.7	V		
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$	V _C	-	17	20.4	V		
Capacitance	at $V_R = 0 V$; f = 1 MHz	CD	-	130	175	pF		
Capacitance	at $V_R = 4 V$; f = 1 MHz	UD UD	-	100	-	pF		

ELECTRICAL CHARACTERISTICS GSOT08C ($T_{amb} = 25$ °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin 1; pin 3 not connected

between pin 1 to pin 2 to pin 1, pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	at I _R = 5 µA	V _{RWM}	-	-	8.5	V		
Reverse current	at V _R = 8.5 V	I _R	-	-	5	μA		
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	9.5	10.7	-	V		
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	11.7	14	V		
neverse clamping voltage	at I _{PP} = I _{PPM} = 18 A	vс	-	18.5	22.2	V		
Capacitance	at $V_R = 0 V$; f = 1 MHz	CD	-	80	125	pF		
Capacitance	at $V_R = 4 V$; f = 1 MHz	ΟD	_	60	-	pF		

ELECTRICAL CHARACTERISTICS GSOT12C (T_{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	at I _R = 1 μA	V _{RWM}	-	-	12.5	V
Reverse current	at V _R = 12.5 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	13.5	15.7	-	V
	at I _{PP} = 1 A	V	-	16.4	19.7	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 12 A	V _C	-	23.4	28.1	V
Canaaitanaa	at $V_R = 0 V$; f = 1 MHz	<u> </u>	-	58	75	pF
Capacitance	at V _R = 7.5 V; f = 1 MHz	C _D	-	36	-	pF



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ELECTRICAL CHARACTERISTICS GSOT15C ($T_{amb} = 25$ °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines	
Reverse stand-off voltage	at I _R = 1 μA	V _{RWM}	-	-	15.5	V	
Reverse current	at V _R = 15.5 V	I _R	-	-	1	μA	
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	17	18.7	-	V	
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	20.4	24.5	V	
	at $I_{PP} = I_{PPM} = 8 A$		-	26.6	30.6	V	
Capacitance	at $V_R = 0 V$; f = 1 MHz	C _D	-	45	60	pF	
	at V _R = 7.5 V; f = 1 MHz		-	25	-	pF	

ELECTRICAL CHARACTERISTICS GSOT24C (T_{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	at I _R = 1 μA	V _{RWM}	-	-	24.5	V
Reverse current	at V _R = 24.5 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	27.5	30.7	-	V
	at I _{PP} = 1 A	V	-	34	41	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 5 A	V _C	-	- 40	48	V
Capacitance	at $V_R = 0 V$; f = 1 MHz	CD	-	33	40	pF
	at V _R = 12 V; f = 1 MHz		-	18	-	pF

ELECTRICAL CHARACTERISTICS GSOT36C ($T_{amb} = 25$ °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines	
Reverse stand-off voltage	at I _R = 1 μA	V _{RWM}	-	-	36.5	V	
Reverse current	at V _R = 36.5 V	I _R	-	-	1	μA	
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	39.5	43.7	-	V	
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	50	60	V	
	at $I_{PP} = I_{PPM} = 3.5 \text{ A}$		-	60	72	V	
Capacitance	at $V_R = 0 V$; f = 1 MHz	CD	-	26	33	pF	
	at V _R = 18 V; f = 1 MHz		-	10	-	pF	



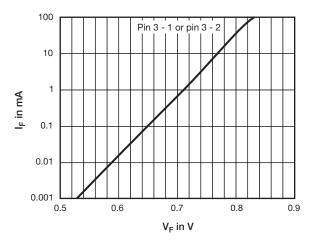


Fig. 1 - Typical Forward Current I_F vs. Forward Voltage V_F

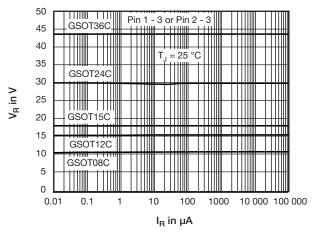


Fig. 2 - Typical Reverse Voltage V_{R} vs. Reverse Current I_{R}

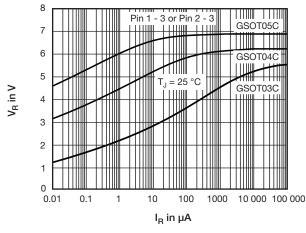
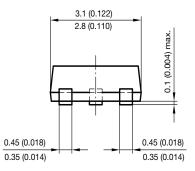


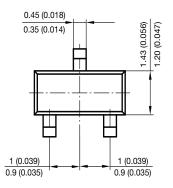
Fig. 3 - Typical Reverse Voltage V_{R} vs. Reverse Current I_{R}

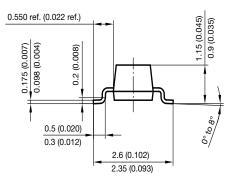


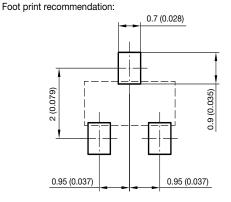
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PACKAGE DIMENSIONS in millimeters (inches): SOT-23

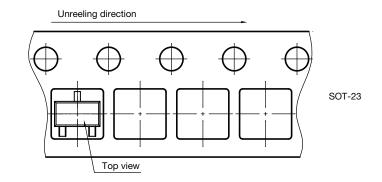








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Orientation in carrier tape SOT-23 S8-V-3929.01-006 (4) 04.02.2010 22607

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